WAFER FABRICATION FLOWCHART

Product: CMOS Products
Package: All Package Types

Location of Wafer Fab: Linear Technology Corp., Milpitas, CA./ Camas, WA

Assembly: Linear Technology Corporation, Penang, Malaysia o

any approved assembly subcontractor

Final Test: Linear Technology Corp., Milpitas, CA., Singapore Q.C. Test: Linear Technology Corp., Milpitas, CA., Singapore Source Accept Test: Linear Technology Corp., Milpitas, CA., Singapore

Quality Contact: Naib Girn, LTC Milpitas, CA

(408) 432-1900 Ext. 2519

	\bigvee	INCOMING
		QUALITY INSPECTION AND GATE
	\bigcirc	MANUFACTURING PROCESS
/A or		QUALITY MONITOR / SURVEILLANCE
		REWORK

FLOW CHART	PROCESS STEP	DESCRIPTION	INSPECTION/TEST CRITERIA	METHOD & EQUIPMENT	SAMPLING PLAN	SPC TECHNIQUE
	INCOMING RAW MATERIAL INSPECTION	WAFERS	VISUAL: SCRATCHES, PITS, HAZE, CRATERS, DIMPLES, CONTAMINATION	1 X INSPECTION	1.0% AQL TO 2.5 AQL LEVEL 1	LOGBOOK
			OXYGEN/CARBON MEASUREMENT	INFRARED SPECTROMETER	S/S=2, ACC = 0	
			RESISTIVITY / CONDUCTIVITY	MAGNETRON V/I METER	S/S=2, ACC = 0	
			DIMENSIONAL	CALIPERS	2.5% AQL, LEVEL 1	
			THICKNESS AND TAPER/BOW	DIAL THICKNESS GAGE	2.5% AQL, LEVEL 1	
			ORIENTATION	BREAK TEST	S/S=1. ACC = 0	
			C OF C VERIFICATION AGAINST "MPS" REQUIREMENTS		EACH BATCH	
		RETICLE	VISUAL, C.D. MEASUREMENTS		EACH PLATE	LOGBOOK
		CHEMICALS	C OF C VERIFICATION AGAINST "MPS" REQUIREMENTS			
		GASES	C OF C VERIFICATION AGAINST "MPS" REQUIREMENTS			
		TARGETS	C OF C VERIFICATION			
\Diamond	INITIAL OXIDATION	OXIDATION FURNACE	VISUAL	UV LAMP MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	LOGBOOK
			OXIDE THICKNESS	NANOSPEC	3 WAFERS / CYCLE	
00	P-WELL MASK	RESIST MASK HF ETCH BATH	VISUAL	OPTICAL MICROSCOPE 100X	"S" PATTERN SCAN OF THE WAFERS	PRODUCTION LOG
\Diamond - \Diamond	PRE IMPLANT OXIDATION	OXIDATION FURNACE	VISUAL	UV LAMP MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	LOGBOOK
			OXIDE THICKNESS	NANOSPEC	3 WAFERS/CYCLE	
\bigcirc	P-WELL IMPLANT	IMPLANT	DOSE CHECK	THERMAWAVE	2 WAFERS/LOT	LOGBOOK
	P-WELL DRIVE	FURNACE	VISUAL	UV LAMP MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	LOGBOOK
			OXIDE THICKNESS	NANOSPEC	3 WAFERS/CYCLE	

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FLOW CHART	PROCESS STEP	DESCRIPTION	INSPECTION/TEST CRITERIA	METHOD & EQUIPMENT	SAMPLING PLAN	SPC TECHNIQUE
ϕ - ϕ	STRIP ALL OXIDE	HF ETCH BATH	VISUAL	UV LAMP MICROSCOPE INSPECTION		LOGBOOK
			OXIDE THICKNESS	NANOSPEC	2 WAFERS /LOT	
	PAD OXIDATION	OXIDATION FURNACE	VISUAL	UV LAMP MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	LOGBOOK
			OXIDE THICKNESS	NANOSPEC	3 WAFERS/CYCLE	
	NITRIDE DEPOSITION	NITRIDE FURNACE	VISUAL	UV LAMP MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	AS APPLICABLE LOGBOOK
			NITRIDE THICKNESS	NANOSPEC	3 WAFERS/CYCLE	
0-0	ACTIVE MASK	RF PLASMA ETCH	VISUAL INSPECTION CRITICAL DIMENSIONS	MICROSCOPE 400X	"S" PATTERN SCAN OF THE WAFERS	PRODUCTION LOG
	P FIELD IMPLANT MASK	RESIST MASK HF ETCH BATH	VISUAL INSPECTION	MICROSCOPE 400X	"S" PATTERN SCAN OF THE WAFERS	PRODUCTION LOG
\Diamond	BORON FIELD IMPLANT	IMPLANT	DOSE CHECK	THERMAWAVE	2 WAFERS / LOT	LOGBOOK
	CMOS STRIP RESIST	RF PLASMA SULFURIC ACID	VISUAL INSPECTION	MICROSCOPE 100X	"S" PATTERN SCAN OF THE WAFERS	LOGBOOK
	N-FIELD IMPLANT MASK	RESIST MASK HF ETCH BATH	UV VISUAL	UV LAMP MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	PRODUCTION LOG
			VISUAL INSPECTION	MICROSCOPE 100X	"S" PATTERN SCAN OF THE WAFERS	
$ \diamondsuit $	PHOS FIELD IMPLANT	IMPLANT	DOSE CHECK	THERMAWAVE	2 WAFERS / LOT	LOGBOOK
\rightarrow	CMOS STRIP RESIST	RF PLASMA SULFURIC ACID	VISUAL INSPECTION	MICROSCOPE 100X	"S" PATTERN SCAN OF THE WAFERS	LOGBOOK
	LOCOS OXIDE	OXIDATION FURNACE	VISUAL	UV LAMP MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	LOGBOOK
			OXIDE THICKNESS	NANOSPEC	3 WAFERS/CYCLE	
\bigcirc	PLASMA NITRIDE STRIP	RF PLASMA ETCH	VISUAL	UV LAMP (100%) 20X MICROSCOPE	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	LOGBOOK
$\overline{\bigcirc}$	CMOS CAP MASK	RESIST MASK HF ETCHANT BATH	CRITICAL DIMENSIONS	OPTICAL MICROSCOPE 100X	"S" PATTERN SCAN OF THE WAFERS	PRODUCTION LOG
\rightarrow	CAP IMPLANT	IMPLANT	DOSE CHECK	THERMAWAVE	2 WAFERS / LOT	LOGBOOK
	CMOS STRIP RESIST	RF PLASMA SULFURIC ACID	VISUAL INSPECTION	MICROSCOPE 100X	"S" PATTERN SCAN OF THE WAFERS	LOGBOOK
	ETCH PAD OXIDE	HF ETCHANT BATH	VISUAL	MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	LOGBOOK
			OXIDE THICKNESS	NANOSPEC	1 WAFER /CYCLE	

FLOW CHART	PROCESS STEP	DESCRIPTION	INSPECTION/TEST CRITERIA	METHOD & EQUIPMENT	SAMPLING PLAN	SPC TECHNIQUE
\Diamond	GATE OXIDE	OXIDATION FURNACE	VISUAL	UV LAMP MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	AS APPLICABLE
			P CH OXIDE THICKNESS	NONOSPEC	3 WAFERS/CYCLE	LOGBOOK
			VISUAL	UV LAMP MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	
			N CH OXIDE THICKNESS	NANOSPEC	3 WAFERS/CYCLE	
	VTP IMPLANT MASK	RESIST MASK HF ETCHANT BATH	VISUAL	OPTICAL MICROSCOPE 100X	"S" PATTERN SCAN OF THE WAFERS	PRODUCTION LOG
	BORON VT IMPLANT	IMPLANT	DOSE CHECK	THEMAWAVE	2 WAFERS/LOT	LOGBOOK
	CMOS STRIP RESIST	RF PLASMA SULFURIC ACID	VISUAL INSPECTION	MICROSCOPE 100X	"S" PATTERN SCAN 100% OF THE WAFERS	LOGBOOK
-	POLY DEPOSITION	FURNACE	POLY THICKNESS	NANOSPEC	2 WAFERS/CYCLE	AS APPLICABLE LOGBOOK CRITICAL NODE
\Diamond	BACK ETCH MASK	RESIST MASK RF PLASMA AND HF ETCH BATH	VISUAL	UV LAMP MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	LOGBOOK
	SINKER PRE DEPOSITION	DEPOSITION FURNACE	VISUAL	UV LAMP MICROSCOPE INSPECTION	100% <10 DEFECTS PER WAFER	TREND CHART
			RS (OHMS/SQ)	4 POINT PROBE	2 TEST WAFERS PER RUN	
0-0	CMOS GATE MASK	RESIST MASK RF PLASMA AND HF ETCHANT BATH	VISUAL INSPECTION	OPTICAL MICROSCOPE 100X	"S" PATTERN SCAN OF THE WAFERS	AS APPLICABLE PRODUCTION LOG CRITICAL NODE
\rightarrow	P+ IMPLANT MASK	RESIST MASK	VISUAL INSPECTION	OPTICAL MICROSCOPE 100X	"S" PATTERN SCAN OF THE WAFERS	PRODUCTION LOG
\(\)	P+ S/D IMPLANT	IMPLANT	DOSE CHECK	THERMAWAFE	2 WAFERS/LOT	LOGBOOK
\rightarrow	CMOS STRIP RESIST	RF PLASMA SULFURIC ACID	VISUAL INSPECTION	MICROSCOPE 100X	"S" PATTERN SCAN OF THE WAFERS	PRODUCTION LOG
Image: Control of the	N+ IMPLANT MASK	RESIST MASK	VISUAL INSPECTION	MICROSCOPE 100X	"S" PATTERN SCAN OF THE WAFERS	LOGBOOK
\Diamond	N+ S/D IMPLANT	IMPLANT	DOSE CHECK	THERMAWAVE	2 WAFERS/LOT	LOGBOOK
Image: Control of the	CMOS STRIP RESIST	RF PLASMA SULFURIC ACID	VISUAL INSPECTION	MICROSCOPE 100X	"S" PATTERN SCAN OF THE WAFERS	LOGBOOK

F	LOW CHART	PROCESS STEP	DESCRIPTION	INSPECTION/TEST CRITERIA	METHOD & EQUIPMENT	SAMPLING PLAN	SPC TECHNIQUE
	}- O	SOURCE DRAIN REOX	OXIDATION FURNACE	VISUAL	UV LAMP MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	LOGBOOK
				P+ OXIDE THICKNESS	NANOSPEC	3 WAFERS/CYCLE	
				VISUAL	UV LAMP MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	
				N+ OXIDE THICKNESS	NANOSPEC	3 WAFERS/CYCLE	
		LPOE	LPOE LPCVD FURNACE	VISUAL	UV LAMP MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	AS APPLICABLE LOGBOOK
				LPOE THICKNESS	NANOSPEC	3 WAFERS/CYCLE	
		CMOS GETTER	FURNACE	RS (OHMS/SQ)	4 POINT PROBE	2 TEST WAFERS PER RUN	TREND CHART
		CMOS CONTACT MASK	RESIST MASK HF ETCHANT BATH	UV VISUAL	UV LAMP MICROSCOPE INSPECTION	2 WAFERS/RUN < 2 DEFECTS PER FIELD OF VIEW	PRODUCTION LOG
				VISUAL INSPECTION	MICROSCOPE 100X	"S" PATTERN SCAN OF THE WAFERS	
		ALUMINUM DEPOSITION	DEPOSITION SPUTTER MACHINE	VISUAL	UV LAMP	<5 DEFECTS PER WAFER 100%	LOGBOOK
				RS (OHMS/SQ)	4 POINT PROBE	2 TEST CHIP/CYCLE	
		CMOS METAL MASK	RESIST MASK METAL ENCHANT BATH	FINAL INSPECT CRITICAL DIMENSIONS	OPTICAL MICROSCOPE 2 200X	"S" PATTERN SCAN OF THE WAFERS	AS APPLICABLE
					1000X	CRITICAL DIMENSIONS MEASURE 2 WAFERS PER RUN LOT, ACCEPT ON 0 FAILURES	PRODUCTION LOG
		ALLOY	ANNEAL FURNACE	VISUAL	UV LAMP	100% <10 DEFECTS PER WAFER	LOGBOOK
		LPOM	PASSIVATION LPCVD FURNACE	VISUAL	UV LAMP	100%, MORE THAN 2 COLOR CHANGE IS FAIL	AS APPLICABLE
) - O				10X MICROSCOPE	3 WAFERS/CYCLE <3 DEFECTS/PER FIELD OF VIEW	
$ \ $				LPOM THICKNESS	NANOSPEC	3 WAFERS/CYCLE	
				PHOSPHOROUS CONCENTRATION	10:1 HF ETCH RATE	3 WAFERS/CYCLE	

FLOW CHART	PROCESS STEP	DESCRIPTION	INSPECTION/TEST CRITERIA	METHOD & EQUIPMENT	SAMPLING PLAN	SPC TECHNIQUE
	PEN	PECVD NITRIDE DEPOSITION	VISUAL	UV LAMP	100%, MORE THAN 2 COLOR CHANGE IS FAIL	TREND CHART
				10X MICROSCOPE	3 WAFERS/CYCLE <5 DEFECTS/PER FIELD OF VIEW	
			PEN THICKNESS	NANOSPEC	3 WAFERS/CYCLE	
			INDEX OF REFRACTION	ELIPSOMETER	3 WAFERS/CYCLE	
ϕ - ϕ	PAD MASK	RESIST MASK RF PLASMA ETCH AND HF ETCHANT BATH	FINAL INSPECT	OPTICAL MICROSCOPE 100X	"S" PATTERN SCAN OF THE WAFER	PRODUCTION LOG
ϕ -O	ELECTRICAL TEST	LOMAC PARAMETRIC ANALYZER			100%	LOGBOOK
\Diamond -O	BACKLAP	DISCO	N/A	N/A	N/A	LOGBOOK
	BACKSIDE GOLD	BACKSIDE METALLIZATION	VISUAL	UN-AIDED EYE	100%	
	SEM	STEP COVERAGE	2 PHOTOS	SCANNING ELECTRON MICROSCOPE	CMOS = 1 WAFER PER WEEK	LOGBOOK
		GENERAL METAL	1 PHOTO		NWELL & PWELL = 1 WAFER EVERY RUN	